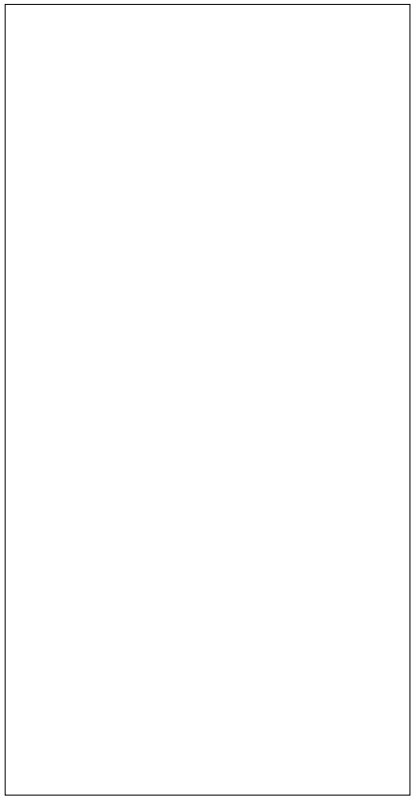
JCT1025A 25A SCR

Rev.A.1.1



Peak gate current (t_p=20μs , T_j=125)	I_{GM}	5	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	40	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	90	mA
I_H	I_T=500mA	-	-	80	mA
dV/dt	V_D=670V Gate Open T_j=125	1200	-	-	V/μs
t_{on}	I_G=50mA I_A=500mA I_R=50mA T_j=25	-	5	-	μs
t_{off}		-	70	-	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=50A t_p=380μs	T_j=25	1.55	V
V_{TO}	Threshold voltage	T_j=125	0.74	V
R_D	Dynamic resistance	T_j=125	19	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	6	μA
I_{RRM}		T_j=125	1.8	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	2	/W
$R_{th(j-a)}$	junction to ambient (DC)	60	/W

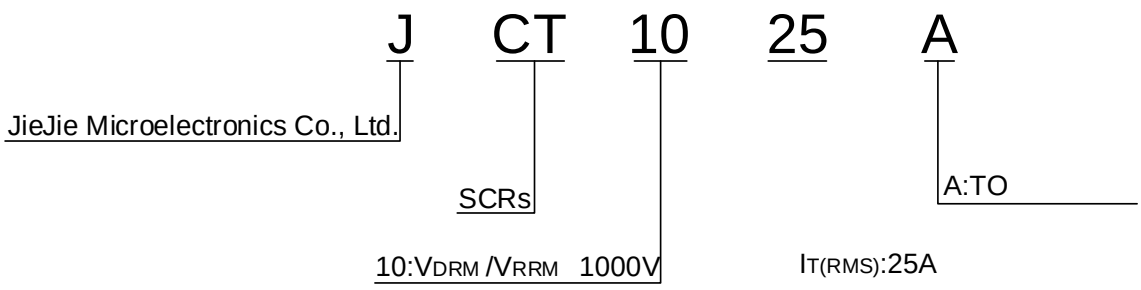

J
CT
10
25
A
JieJie Microelectronics Co., Ltd.
SCRs
A:TO
10:VDRM /VRRM 1000V
IT(RMS):25A

FIG.1: Maximum power dissipation versus RMS on-state current

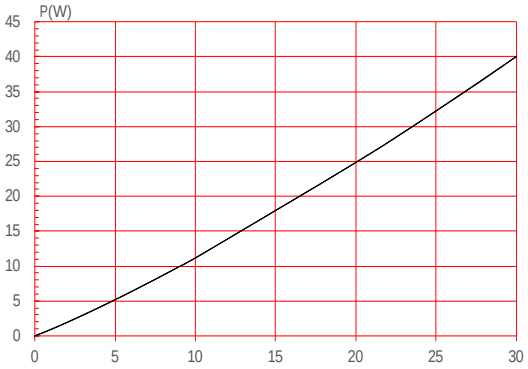
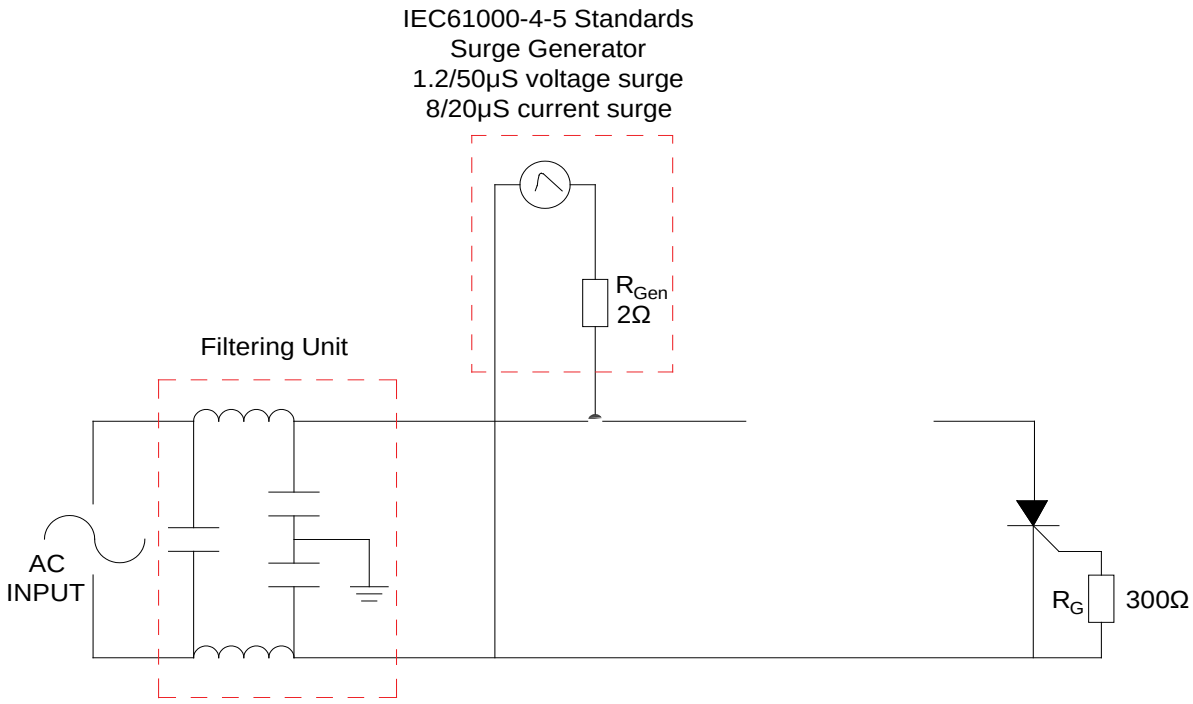
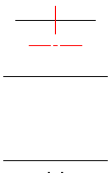


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.